

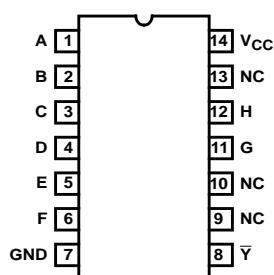
## Features

- Buffered Inputs
- Typical Propagation Delay: 10ns at  $V_{CC} = 5V$ ,  $C_L = 15pF$ ,  $T_A = 25^\circ C$
- Fanout (Over Temperature Range)
  - Standard Outputs ..... 10 LSTTL Loads
  - Bus Driver Outputs ..... 15 LSTTL Loads
- Wide Operating Temperature Range ... -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}, V_{OH}$

## Pinout

CD54HC30, CD54HCT30 (CERDIP)  
 CD74HC30 (PDIP, SOIC, SOP, TSSOP)  
 CD74HCT30 (PDIP, SOIC)

### TOP VIEW



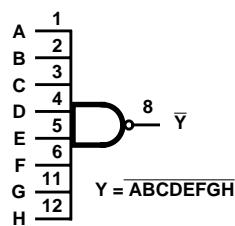
## Description

The 'HC30 and 'HCT30 each contain an 8-input NAND gate in one package. They provide the system designer with the direct implementation of the positive logic 8-input NAND function. Logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The HCT logic family is functionally pin compatible with the standard LS logic family.

## Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC30F3A	-55 to 125	14 Ld CERDIP
CD54HCT30F3A	-55 to 125	14 Ld CERDIP
CD74HC30E	-55 to 125	14 Ld PDIP
CD74HC30M	-55 to 125	14 Ld SOIC
CD74HC30MT	-55 to 125	14 Ld SOIC
CD74HC30M96	-55 to 125	14 Ld SOIC
CD74HC30NSR	-55 to 125	14 Ld SOP
CD74HC30PW	-55 to 125	14 Ld TSSOP
CD74HC30PWR	-55 to 125	14 Ld TSSOP
CD74HC30PWT	-55 to 125	14 Ld TSSOP
CD74HCT30E	-55 to 125	14 Ld PDIP
CD74HCT30M	-55 to 125	14 Ld SOIC
CD74HCT30MT	-55 to 125	14 Ld SOIC
CD74HCT30M96	-55 to 125	14 Ld SOIC

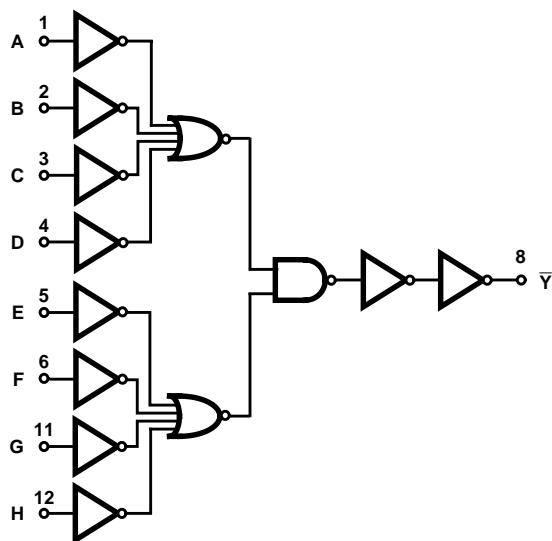
NOTE: When ordering, use the entire part number. The suffixes 96 and R denote tape and reel. The suffix T denotes a small-quantity reel of 250.

***Functional Diagram***

TRUTH TABLE

INPUTS								OUTPUT
A	B	C	D	E	F	G	H	
L	X	X	X	X	X	X	X	H
X	L	X	X	X	X	X	X	H
X	X	L	X	X	X	X	X	H
X	X	X	L	X	X	X	X	H
X	X	X	X	L	X	X	X	H
X	X	X	X	X	L	X	X	H
X	X	X	X	X	X	L	X	H
X	X	X	X	X	X	X	L	H
H	H	H	H	H	H	H	H	L

NOTE: H = HIGH Voltage Level, L = LOW Voltage Level, X = Irrelevant

***Logic Symbol***

**Absolute Maximum Ratings**

DC Supply Voltage, V <sub>CC</sub> .....	-0.5V to 7V
DC Input Diode Current, I <sub>IK</sub>	
For V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> + 0.5V .....	±20mA
DC Output Diode Current, I <sub>OK</sub>	
For V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> + 0.5V .....	±20mA
DC Output Source or Sink Current per Output Pin, I <sub>O</sub>	
For V <sub>O</sub> > -0.5V or V <sub>O</sub> < V <sub>CC</sub> + 0.5V .....	±25mA
DC V <sub>CC</sub> or Ground Current, I <sub>CC</sub> or I <sub>GND</sub> .....	±50mA

**Thermal Information**

Package Thermal Impedance, θ <sub>JA</sub> (see Note 1)	
E (PDIP) Package .....	80°C/W
M (SOIC) Package .....	86°C/W
NS (SOP) Package .....	76°C/W
PW (TSSOP) Package .....	113°C/W
Maximum Junction Temperature (Hermetic Package or Die) .....	175°C
Maximum Junction Temperature (Plastic Package) .....	150°C
Maximum Storage Temperature Range .....	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) .....	300°C
(SOIC - Lead Tips Only)	

**Operating Conditions**

Temperature Range (T <sub>A</sub> ) .....	-55°C to 125°C
Supply Voltage Range, V <sub>CC</sub>	
HC Types .....	.2V to 6V
HCT Types .....	.45V to 5.5V
DC Input or Output Voltage, V <sub>I</sub> , V <sub>O</sub> .....	0V to V <sub>CC</sub>
Input Rise and Fall Time	
2V .....	1000ns (Max)
4.5V .....	500ns (Max)
6V .....	400ns (Max)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

## NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

**DC Electrical Specifications**

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO +85°C		-55°C TO 125°C		UNITS	
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX		
<b>HC TYPES</b>													
High Level Input Voltage	V <sub>IH</sub>	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
				4.5	3.15	-	-	3.15	-	3.15	-	V	
				6	4.2	-	-	4.2	-	4.2	-	V	
Low Level Input Voltage	V <sub>IL</sub>	-	-	2	-	-	0.5	-	0.5	-	0.5	V	
				4.5	-	-	1.35	-	1.35	-	1.35	V	
				6	-	-	1.8	-	1.8	-	1.8	V	
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	2	1.9	-	-	1.9	-	1.9	-	V	
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V	
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V	
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V	
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V	
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V	
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	2	-	-	0.1	-	0.1	-	0.1	V	
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V	
			0.02	6	-	-	0.1	-	0.1	-	0.1	V	
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V	
			4	4.5	-	-	0.26	-	0.33	-	0.4	V	
			5.2	6	-	-	0.26	-	0.33	-	0.4	V	
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	µA	

# CD54/74HC30, CD54/74HCT30

## DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO +85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	6	-	-	2	-	20	-	40	μA
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> and GND	-	5.5	-		±0.1	-	±1	-	±1	μA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	2	-	20	-	40	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 2)	ΔI <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA

NOTE:

2. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

## HCT Input Loading Table

INPUT	UNIT LOADS
All	0.6

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Specifications table, e.g. 360μA max at 25°C.

## Switching Specifications Input t<sub>r</sub>, t<sub>f</sub> = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
Propagation Delay, Input to Output (Figure 1)	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 50pF	2	-	-	130	-	165	-	195	ns
			4.5	-	-	26	-	33	-	39	ns
			6	-	-	22	-	28	-	33	ns
Propagation Delay, Data Input to Output Y	t <sub>PLH</sub> , t <sub>PHL</sub>	C <sub>L</sub> = 15pF	5	-	10	-	-	-	-	-	ns

**Switching Specifications** Input  $t_r, t_f = 6\text{ns}$  (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Transition Times (Figure 1)	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	$C_I$	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 3, 4)	$C_{PD}$	-	5	-	25	-	-	-	-	-	pF
<b>HCT TYPES</b>											
Propagation Delay, Input to Output (Figure 2)	$t_{RHL}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	-	28	-	35	-	42	ns
Propagation Delay, Data Input to Output Y	$t_{PLH}, t_{PHL}$	$C_L = 15\text{pF}$	5	-	11	-	-	-	-	-	ns
Transition Times (Figure 2)	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	$C_I$	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 3, 4)	$C_{PD}$	-	5	-	26	-	-	-	-	-	pF

## NOTES:

3.  $C_{PD}$  is used to determine the dynamic power consumption, per gate.  
 4.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

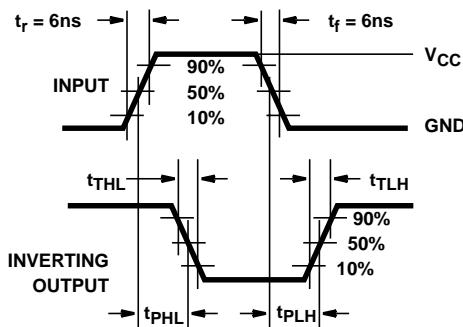
**Test Circuits and Waveforms**

FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

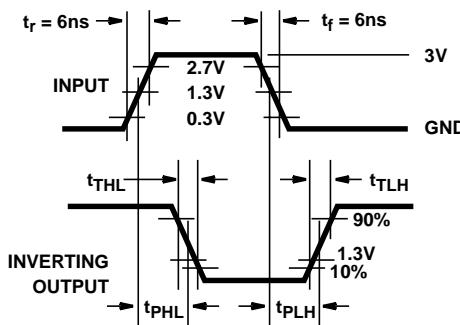


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC